

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	717	CMOS same implant\$4 same anneal\$3	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:39
L2	229	CMOS same implant\$4 same anneal\$3 same polysilicon	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 08:53
L3	18	2 and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 08:21
L4	3	CMOS same implant\$4 same anneal\$3 same (polysilicon with resistor)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 08:54
L5	39	CMOS and implant\$4 and anneal\$3 and (polysilicon with resistor) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:39
L9	96	CMOS same implant\$4 same (anneal\$3 and heat\$4)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:39
L10	53	CMOS and (implant\$4 or dop\$4) and (anneal\$3 or heat\$4) and (polysilicon with resistor) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:41
L11	933	CMOS and (implant\$4 or dop\$4) and (anneal\$3 or heat\$4) and (polysilicon or conductive) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:40
L12	952	CMOS and (implant\$4 or dop\$4) and (anneal\$3 or heat\$4) and (polysilicon or titanium or cobalt or nickel) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:41
L13	76	(titanium or ti or cobalt or Nickel) and (implant\$4 or dop\$4) and (anneal\$3 or heat\$4) and (polysilicon with resistor) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:42
L14	1077	(titanium or ti or cobalt or Nickel) and (implant\$4 or dop\$4) and (anneal\$3 or heat\$4) and polysilicon and (resistor or resistance) and silicidation	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:43

L15	608	14 and CMOS	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/05/03 09:43
-----	-----	-------------	--	----	-----	------------------